

### NDT456P

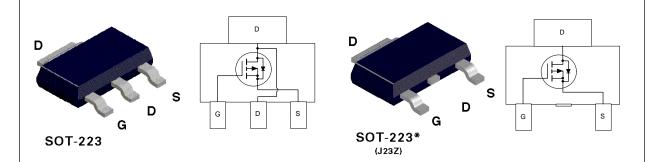
## P-Channel Enhancement Mode Field Effect Transistor

### **General Description**

Power SOT P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management, battery powered circuits, and DC motor control.

#### **Features**

- High density cell design for extremely low R<sub>DS(ON)</sub>.
- High power and current handling capability in a widely used surface mount package.



Absolute Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

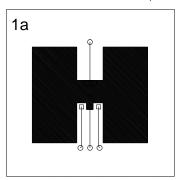
Symbol	Parameter		NDT456P	Units V	
DSS	Drain-Source Voltage		-30		
GSS	Gate-Source Voltage		±20		
	Drain Current - Continuous	(Note 1a)	±7.5	А	
	- Pulsed		±20		
D	Maximum Power Dissipation	(Note 1a)	3	W	
		(Note 1b)	1.3		
		(Note 1c)	1.1		
,T <sub>STG</sub>	Operating and Storage Temperature	Range	-65 to 150	℃	
HERMA	L CHARACTERISTICS				
θJA	Thermal Resistance, Junction-to-Am	bient (Note 1a)	42	°C/W	
- BJC	Thermal Resistance, Junction-to-Cas	SE (Note 1)	12	°C/W	

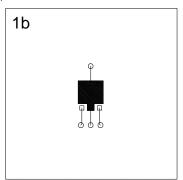
Symbol	Parameter	Conditions	Min	Тур	Max	Units	
OFF CHA	RACTERISTICS						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$		-30			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μΑ	
			$T_J = 55^{\circ}C$			-10	μΑ
GSSF	Gate - Body Leakage, Forward	$V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	·			100	nA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$				-100	nA
ON CHAR	ACTERISTICS (Note 2)			•	•		
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-1	-1.5	-3	V
			T <sub>J</sub> = 125°C	-0.5	-1.1	-2.6	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS} = -10 \text{ V}, I_{D} = -7.5 \text{ A}$			0.026	0.03	Ω
			T <sub>J</sub> = 125°C		0.035	0.054	
		$V_{GS} = -4.5 \text{ V}, I_{D} = -6 \text{ A}$			0.041	0.045	
I <sub>D(on)</sub>	On-State Drain Current $V_{GS} = -10 \text{ V}$ , $V_{DS} = -5 \text{ V}$						Α
		$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$		-10			
G <sub>fs</sub>	Forward Transconductance	$V_{GS} = -10 \text{ V}, I_{D} = -7.5 \text{ A}$			13		S
DYNAMIC	CHARACTERISTICS						
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -15 \text{ V}, \ V_{GS} = 0 \text{ V},$					pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz			905		pF
C <sub>rss</sub>	Reverse Transfer Capacitance				355		pF
SWITCHIN	G CHARACTERISTICS (Note 2)						
t <sub>D(on)</sub>	Turn - On Delay Time	$V_{DD} = -15 \text{ V}, I_{D} = -7 \text{ A},$			10	20	ns
t,	Turn - On Rise Time	$V_{GEN}$ = -10 V, $R_{GEN}$ = 12 $\Omega$			65	120	ns
t <sub>D(off)</sub>	Turn - Off Delay Time				70	130	ns
t <sub>r</sub>	Tum - Off Fall Time				70	130	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10 \text{ V},$ $I_D = -7.5 \text{ A}, V_{GS} = -10 \text{ V}$			47	67	nC
$Q_{gs}$	Gate-Source Charge	$I_D = -7.5 \text{ A}, V_{GS} = -10 \text{ V}$			5		nC
$Q_{gd}$	Gate-Drain Charge				12		nC

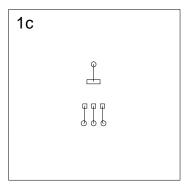
Electrical Characteristics (T <sub>A</sub> = 25°C unless otherwise noted)									
Symbol	Parameter Conditions Min Typ Max U								
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS									
Is	Maximum Continuous Drain-Source Diode Forward Current -2.5								
V <sub>SD</sub>	Drain-Source Diode Forward Voltage		- 0.85	-1.2	V				
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_F = -2.5 \text{ A } dI_F/dt = 100 \text{ A/}\mu\text{s}$			140	ns			

### Notes:

- Notes: 1.  $P_D(t) = \frac{T_J T_A}{R_{BJA}(t)} = \frac{T_J T_A}{R_{BJC} + R_{BCA}(t)} = I_D^2(t) \times R_{DS(ON)@T_J} R_{_{BJA}}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{_{BJC}}$  is guaranteed by design while  $R_{_{BCA}}$  is defined by users. For general reference: Applications on 4.5\*x5\* FR-4 PCB under still air environment, typical  $R_{_{BJA}}$  is found to be:
  - a. 42°C when mounted on a 1 in² pad of 2oz copper.
  - b. 95°C when mounted on a 0.066in² pad of 2oz copper.
  - c. 110°C/W when mounted on a 0.00123in² pad of 2oz copper.







Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%.

## **Typical Electrical Characteristics**

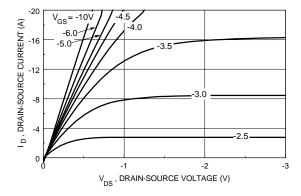


Figure 1. On-Region Characteristics.

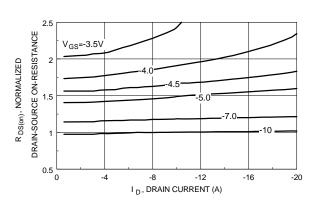


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

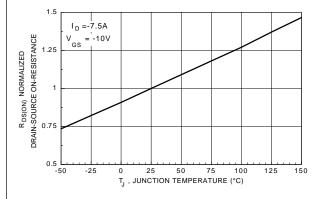


Figure 3. On-Resistance Variation with Temperature.

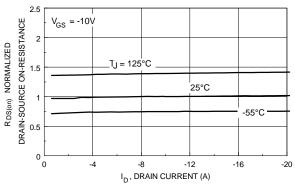


Figure 4. On-Resistance Variation with Drain Current and Temperature.

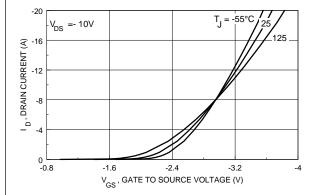


Figure 5. Transfer Characteristics.

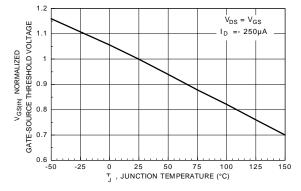


Figure 6. Gate Threshold Variation with Temperature.

### **Typical Electrical Characteristics**

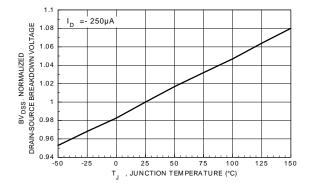


Figure 7. Breakdown Voltage Variation with Temperature.

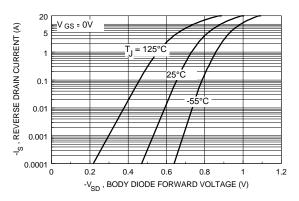


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

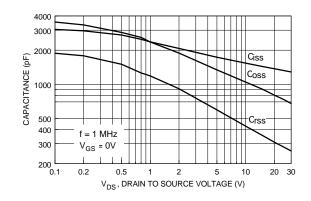


Figure 9. Capacitance Characteristics.

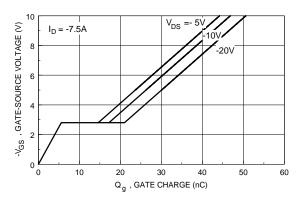


Figure 10. Gate Charge Characteristics.

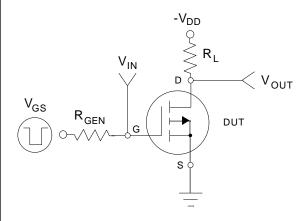


Figure 11. Switching Test Circuit.

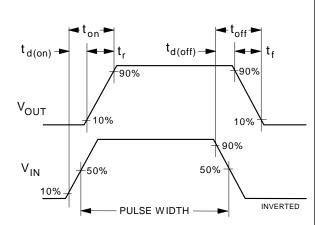
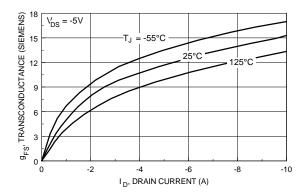


Figure 12. Switching Waveforms.

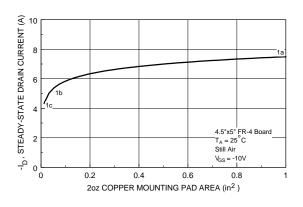
## **Typical Thermal Characteristics**



3.5 STEADY-STATE POWER DISSIPATION (W) 3 1.5 .4.5"x5" FR-4 Board T<sub>A</sub> = 25° C Still Air 0.4 0.6 0.8 20z COPPER MOUNTING PAD AREA (in 2)

Figure 13. Transconductance Variation with Drain **Current and Temperature.** 

Figure 14. SOT-223 Maximum Steady-State Power **Dissipation versus Copper Mounting Pad** Area.



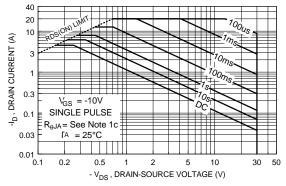


Figure 15. Maximum Steady-State Drain **Current versus Copper Mounting Pad** Area.

Figure 16. Maximum Safe Operating Area.

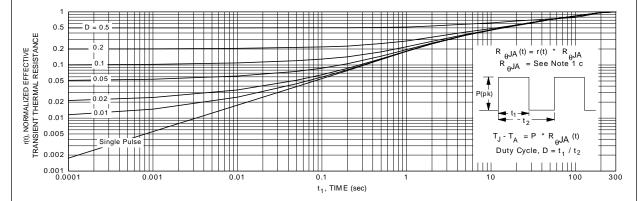
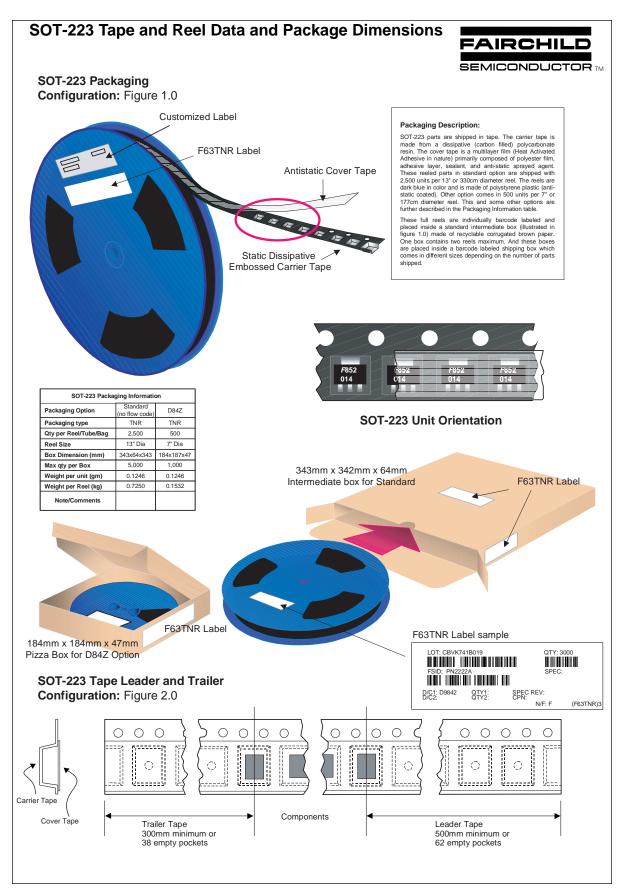


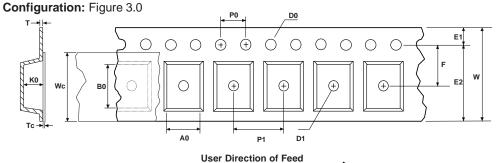
Figure 17. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1c. Transient thermal response will change depending on the circuit board design.



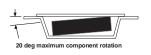


### **SOT-223 Embossed Carrier Tape**

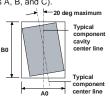


Dimensions are in millimeter														
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.3	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.88 +/-0.10	0.292 +/- 0.0130	9.5 +/-0.025	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



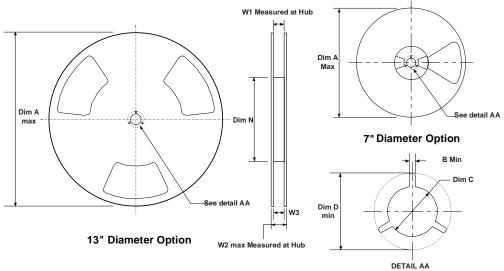
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

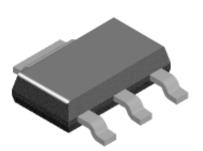
# **SOT-223 Reel Configuration:** Figure 4.0

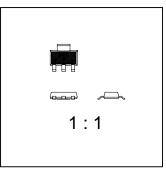


Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	5.906 150	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4
12mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	7.00 178	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.469 - 0.606 11.9 - 15.4

## SOT-223 Tape and Reel Data and Package Dimensions, continued

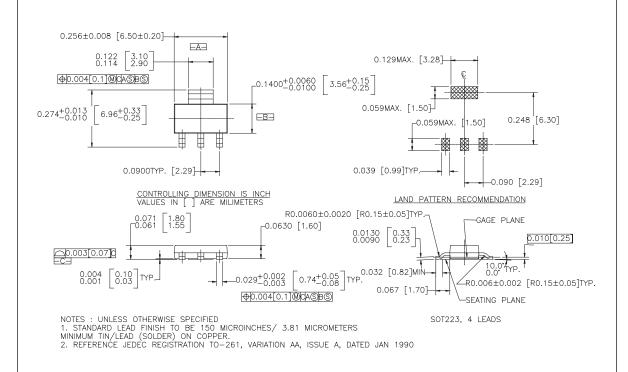
# SOT-223 (FS PKG Code 47)





Scale 1:1 on letter size paper

Part Weight per unit (gram): 0.1246



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